

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. .... 09/653,149  
Confirmation No. .... 4634  
Filing Date .... August 31, 2000  
Inventor .... Garo J. Derderian, et al.  
Assignee .... Micron Technology, Inc.  
Group Art Unit .... 2818  
Examiner .... T. Lee  
Attorney's Docket No. .... MI22-1330  
Customer No. .... 021567  
Title: Capacitor Fabrication Methods Including Forming a Conductive Layer

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

To: Commissioner for Patents  
PO Box 1450  
Art Unit 2818  
Alexandria, VA 22313-1450

From: James E. Lake (Tel. 509-624-4276; Fax 509-838-3424)  
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**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

The Examiner's attention is directed to the references which are listed on the attached Form PTO-1449. Pursuant to 37 C.F.R. §1.98(a)(2)(1) no copies of any cited U.S. patents or U.S. published applications are included herewith. Copies of all other cited art references, if any, are attached. No admission is made regarding whether all the submitted references are prior art.

Citation of these references is respectfully requested.

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Respectfully submitted,

Date:

11 Mar 2005

By:

  
James E. Lake  
Reg. No. 44,854

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U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
MI22-1330SERIAL NO.  
09/653,149LIST OF REFERENCES BY APPLICANT  
(Use several sheets if necessary)

APPLICANT Garo J. Derderian

FILING DATE  
August 31, 2000GROUP  
2818

## U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	6,482,740	11/2002	Soininen et al			
	AB	5,908,947	06/1999	Vaartstra			
	AC	2002/0142488	10/2002	Hong, Suk-Kyoung			
	AD	6,403,156	06/2002	Jang			
	AE	6,746,930	06/2004	Yang			
	AF	2005/0018381	1/2005	McClure			
	AG						
	AH						
	AI						
	AJ						
	AK						

## FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AL							
	AM							
	AN							

## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

	AO		Ritala et al, "Perfectly Conformal TiN and Al2O3 Films Deposited by Atomic Layer Deposition," Chemical Vapor Deposition, v. 5, No. 1, 1999, pp. 7-9.
	AP		Suntola, "Surface Chemistry of Materials Deposition at Atomic Layer Level," Applied Surface Science, vol. 100/101, March 1996, pp. 391-398
	AQ		T. Suntola, Atomic Layer Epitaxy, Handbook of Crystal Growth, Vol. 3, 1994, pp. 603-663.
			Leskela and Ritala, ALD Precursor Chemistry: Evolution and Future Challenges, J. Phys. IV France 9 (1999), pages 837-852.

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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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LIST OF ARTS CITED BY APPLICANT  
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SERIAL NO.  
09/653,149

APPLICANT Garo J. Derderian

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	AA	09/653,156		Agarwal (as amended 10/2003, 3/2004, and 12/2004)			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

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